

REMARKS

Upon entry of the above amendments, claims 3-9, 11-14, 16, 17, 19, 20, 22-27 and 31 will be pending. Applicants proposed cancellation of claims 10 and 18, and amendment of claims 5, 8 and 19. The propose amendments are shown in the attached "**Version with Markings to Show Changes Made.**" Entry of the amendments after final rejection is earnestly solicited.

Amendment of claim 19 is proposed to incorporate the features of claim 18, which have been indicated to be allowable. Amendment of claims 5 and 8 is proposed in response to the rejection under 35 USC § 112, second paragraph.

Claim 4 was rejected under 35 USC § 112, second paragraph, as being indefinite. As noted above, amendment of claims 5 and 8 is proposed to specify that the first insulating film includes at least an organic SOG film. It is believed that the proposed amended claims are in full compliance with 35 USC § 112.

Claims 3, 8, 9, 11-14, 17 and 19 were rejected under 35 USC § 103(a) as being unpatentable over *Brennan et al.* as set forth in paragraph 22 of the previous Office Action. In the previous Office Action, claim 17 was indicated to be allowed, and therefore, it is believed that the inclusion of claim 17 in the rejection is a typographical error. Favorable reconsideration of the rejection is earnestly solicited.

Brennan et al. does not teach or suggest that an organic SOG film is used as the first insulating film and introducing impurities to a surface of the organic SOG film. The claimed invention allows the polishing rate of the SOG film to be improved to a level substantially equal to

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the polishing rate of a silicon oxide film such as TEOS film formed by CVD. Accordingly, it would not have been obvious for one of ordinary skill in the art to employ an SOG film in place of the TEOS film as disclosed by *Brennan et al.*

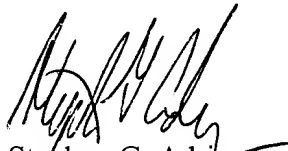
For at least the foregoing reasons, the claimed invention distinguishes over the cited art and defines patentable subject matter. Favorable reconsideration is earnestly solicited.

Should the Examiner deem that any further action by applicants would be desirable to place the application in better condition for allowance, the Examiner is encouraged to telephone applicants' undersigned attorney.

In the event that this paper is not timely filed, Applicants respectfully petition for an appropriate extension of time. Please charge any fees for such an extension of time and any other fees which may be due with respect to this paper, to Deposit Account No. 01-2340.

Respectfully submitted,

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PATENT TRADEMARK OFFICE

Enclosure: Version with markings to show changes made

IN THE CLAIMS:

Claims 5, 8 and 19 have been amended as follows:

5. (Three Times Amended) A fabrication method of a semiconductor device comprising the steps of:

forming a first insulation film, including at least an organic SOG film, on a substrate,

forming a second insulation film [, including at least an organic SOG film,] on said first insulation film,

introducing impurities at least to a surface of said first insulation film either before or after forming said second insulation film, and

effecting planarization by polishing at least said second insulation film,

wherein said step of introducing impurities comprises the steps of

forming a photoresist on a surface of a device before impurities are introduced to said first insulation film, and

introducing impurities into said first insulation film via said photoresist film.

8. (Four Times Amended) A fabrication method of a semiconductor device comprising the steps of:

forming a first insulation film, including at least an organic SOG film, on a substrate,
forming a second insulation film[, including at least an organic SOG film,] on said first insulation film,
introducing impurities at least to a surface of said first insulation film either before or after forming said second insulation film, and
effecting planarization by polishing at least said second insulation film.

19. (Three Times Amended) A fabrication method of a semiconductor device comprising the steps of:
forming a first insulation film, including at least an organic SOG film, on a substrate,
introducing impurities at least to a surface of said first insulation film, [and]
effecting planarization by polishing said first insulation film, and
forming a second insulation film on a surface of a device before said first insulation film is formed.

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